

Features

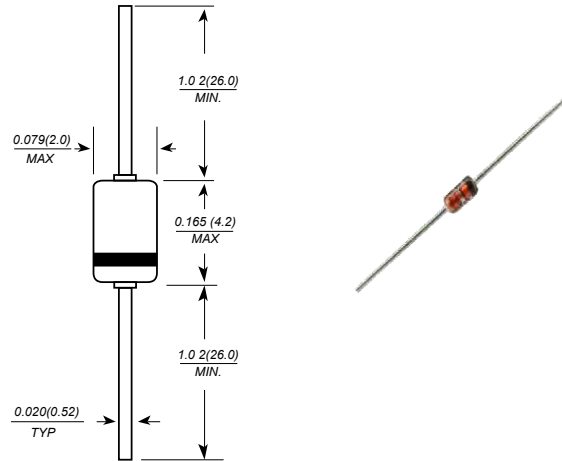
- Silicon epitaxial planar diode
- Fast switching diodes

Mechanical Data

- Case: DO-35, glass case
- Polarity: Color band denotes cathode
- Weight: 0.004 ounces, 0.13 grams



DO-35(GLASS)



Dimensions in millimeters

Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise specified

Type	Peak reverse voltage $V_{RM}(V)$	Max. Aver. Rectified Current $I(AV)Ma$	Max. Power Dissip At 25°C $P_{tot}(mW)$	Max. Junction temperature T_J $^\circ\text{C}$	Max. Forward Voltage drop		Max. Reverse Current		Max. Reverse Recovery Time	
					V_F (V)	at I_F (mA)	I_R (nA)	at $V_R(V)$	$t_{rr}(ns)$ Max.	Test conditions
1N914	100	75	500	200	1.0	10	25	20	4.0	$I_F=10mA, V_R=6V, R_L=100\Omega, \text{ to } I_R=1mA$
1N4149	100	150	500	200	1.0	10	25	20	4.0	$I_F=10mA, V_R=6V, R_L=100\Omega, \text{ to } I_R=1mA$
1N4150	50	200	500	200	1.0	200	100	50	4.0	$I_F=I_R=10 \text{ to } 200mA, \text{ to } 0.1 I_F$
1N4152	40	150	400	175	0.55	0.10	50	30	2.0	$I_F=10mA, V_R=6V, R_L=100\Omega, \text{ to } I_R=1mA$
1N4153	75	150	400	175	0.55	0.10	50	50	2.0	$I_F=10mA, V_R=6V, R_L=100\Omega, \text{ to } I_R=1mA$
1N4154	35	150 ₂₎	500	200	1.0	0.10	100	25	2.0	$I_F=10mA, V_R=6V, R_L=100\Omega, \text{ to } I_R=1mA$
1N4447	100	150	500	200	1.0	20	25	20	4.0	$I_F=10mA, V_R=6V, R_L=100\Omega, \text{ to } I_R=1mA$
1N4449	100	150	500	200	1.0	30	25	20	4.0	$I_F=10mA, V_R=6V, R_L=100\Omega, \text{ to } I_R=1mA$
1N4450	40	150	400	175	0.54	0.50	50	30	4.0	$I_F=I_R=10mA \text{ to, } I_R=1mA$
1N4451	40	150	400	175	0.50	0.10	50	30	10	$I_F=I_R=10mA \text{ to, } I_R=1mA$
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1.0	10	100	50	4.0	$I_F=I_R=10mA \text{ to, } I_R=1mA$

Notes: Valid provided that leads at a distance of 8mm from case are kept at ambient temperature parameters for diodes

in case DO-34: $P_{tot}=300mW$ $T_{STG}=-65 \text{ to } +175^\circ\text{C}$ $T_J=175^\circ\text{C}$ $R_{\theta JA}=400K/W$